



General Description

- Trench Power MOSFET technology
- Low $R_{DS(ON)}$ at 4.5V Vgs
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

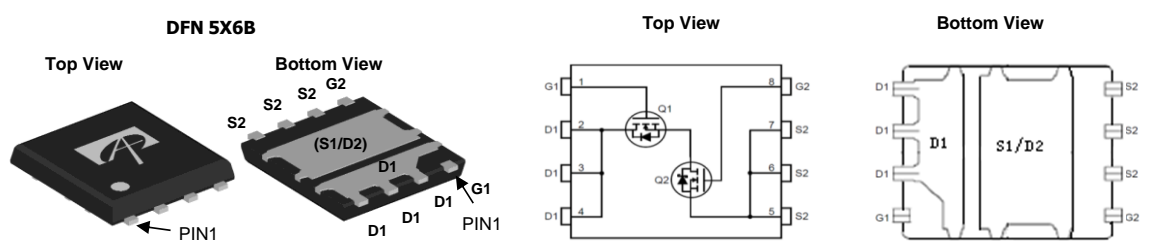
Applications

- DC/DC Converters in Computer
- See Note I

Product Summary

	<u>Q1</u>	<u>Q2</u>
V_{DS}	30V	30V
I_D (at $V_{GS}=10V$)	32A	32A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 6.1m Ω	< 3.8m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 9.6m Ω	< 4.7m Ω

100% UIS Tested
100% Rg Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AONY36356	DFN 5x6B	Tape & Reel	3000

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Max Q1	Max Q2	Units
Drain-Source Voltage	V_{DS}	30	30	V
Gate-Source Voltage	V_{GS}	± 20	± 12	V
Continuous Drain Current ^G	I_D	$T_C=25^\circ C$	32	A
		$T_C=100^\circ C$	30	
Pulsed Drain Current ^C	I_{DM}	114	128	A
Continuous Drain Current	I_{DSM}	$T_A=25^\circ C$	17.5	A
		$T_A=70^\circ C$	14	
Avalanche Current ^C	I_{AS}	55	36	A
Avalanche energy $L=0.01mH$ ^C	E_{AS}	15	6	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ C$	22	W
		$T_C=100^\circ C$	8.7	
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ C$	2.9	W
		$T_A=70^\circ C$	1.9	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ Q1	Typ Q2	Max Q1	Max Q2	Units
Maximum Junction-to-Ambient ^A $t \leq 10s$	$R_{\theta JA}$	35	30	42	36	$^\circ C/W$
Maximum Junction-to-Ambient ^{A,D} Steady-State		65	60	82	75	$^\circ C/W$
Maximum Junction-to-Case Steady-State	$R_{\theta JC}$	4.5	3	5.7	3.8	$^\circ C/W$

Q1 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.3	1.7	2.1	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		5.1	6.1	mΩ
		V _{GS} =4.5V, I _D =20A		7.2	8.8	
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		100		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current				30	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		920		pF
C _{oss}	Output Capacitance			300		pF
C _{riss}	Reverse Transfer Capacitance			35		pF
R _g	Gate resistance	f=1MHz	1.1	2.2	3.3	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =20A		13	20	nC
Q _g (4.5V)	Total Gate Charge			6	9	
Q _{gs}	Gate Source Charge			2.5		
Q _{gd}	Gate Drain Charge			2		
t _{D(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω		7		ns
t _r	Turn-On Rise Time			3.5		
t _{D(off)}	Turn-Off Delay Time			20.5		
t _f	Turn-Off Fall Time			2.5		
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=500A/μs		11		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=500A/μs		18		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

I. For application requiring slow >1ms turn-on/turn-off, please consult AOS FAE for proper product selection.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

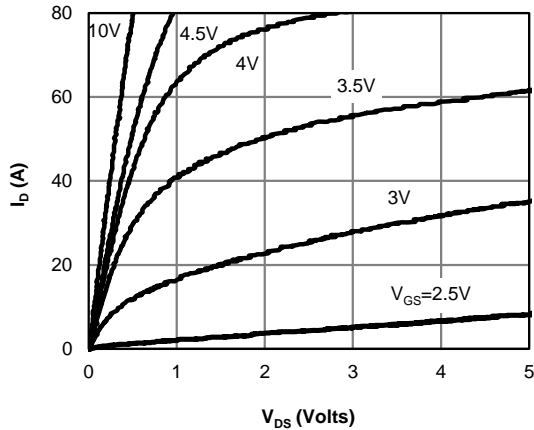


Figure 1: On-Region Characteristics (Note E)

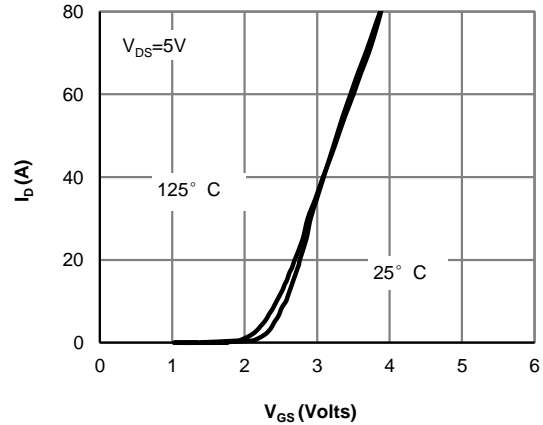


Figure 2: Transfer Characteristics (Note E)

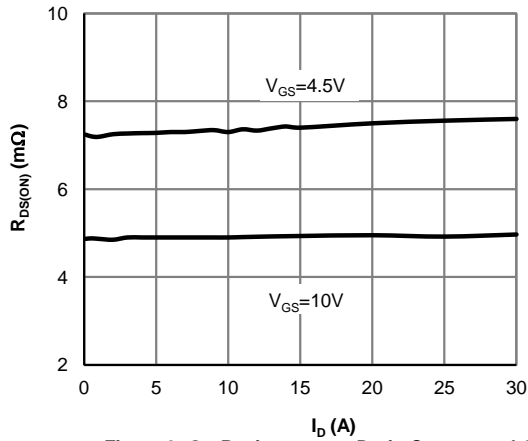


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

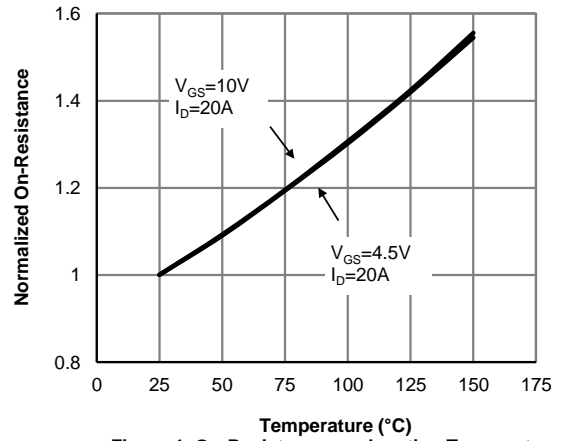


Figure 4: On-Resistance vs. Junction Temperature (Note E)

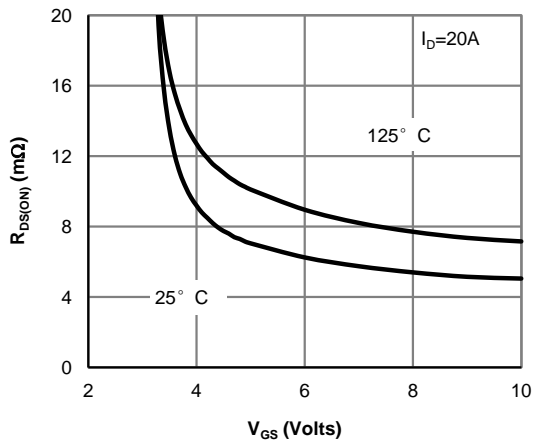


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

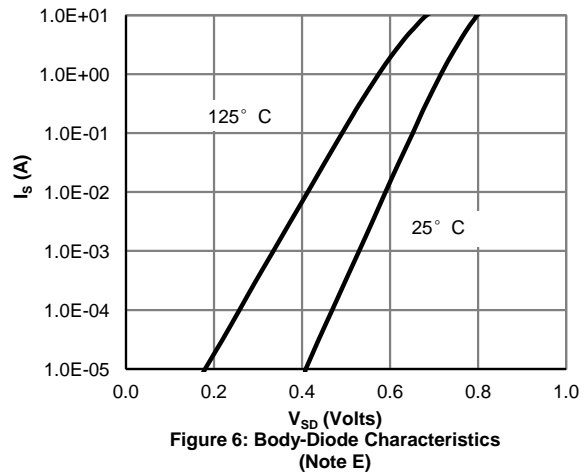


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

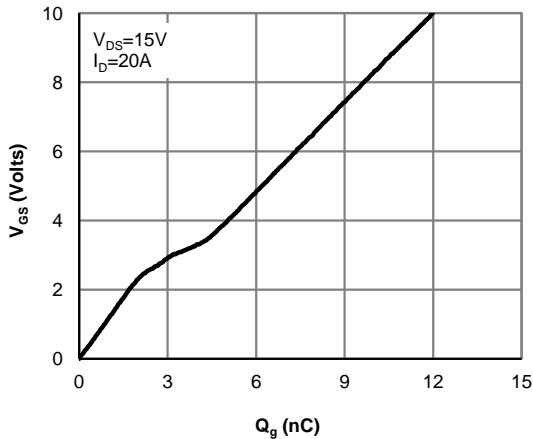


Figure 7: Gate-Charge Characteristics

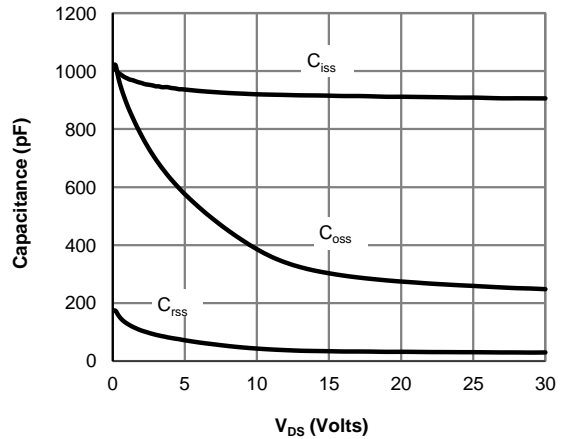


Figure 8: Capacitance Characteristics

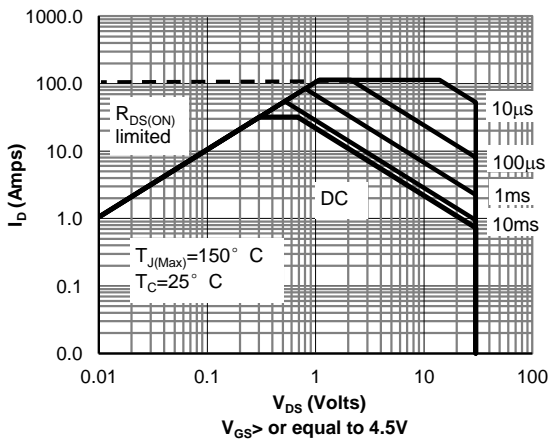


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

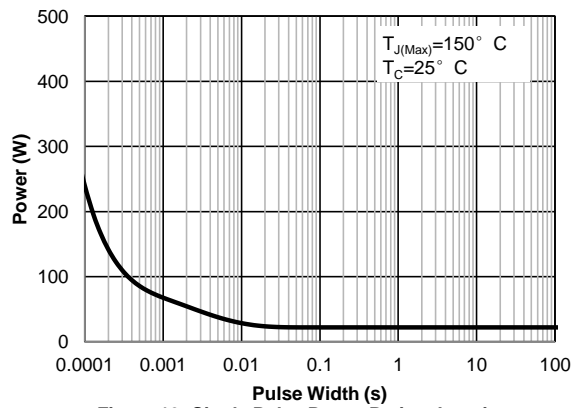


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

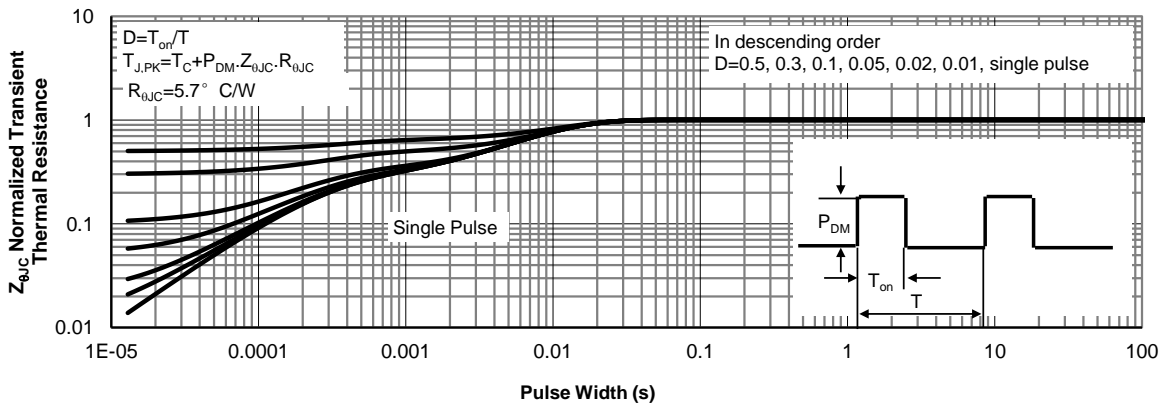


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

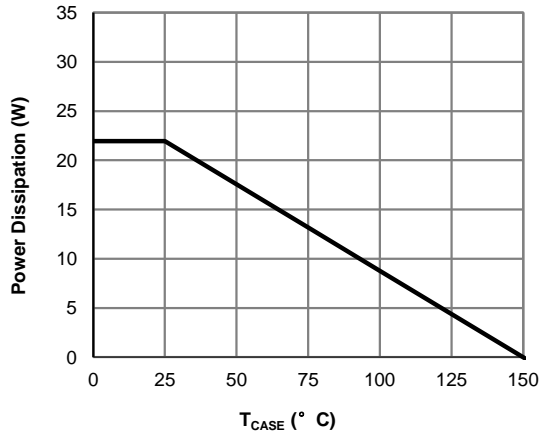


Figure 12: Power De-rating (Note F)

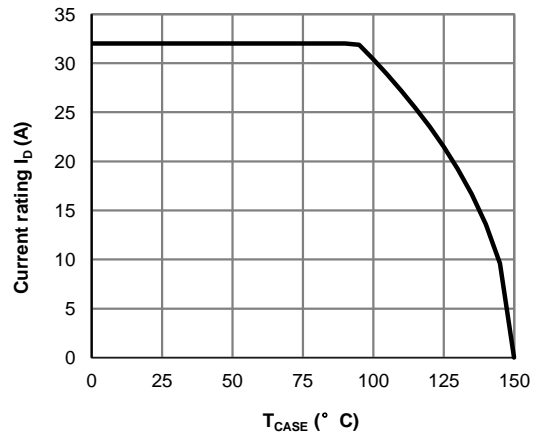


Figure 13: Current De-rating (Note F)

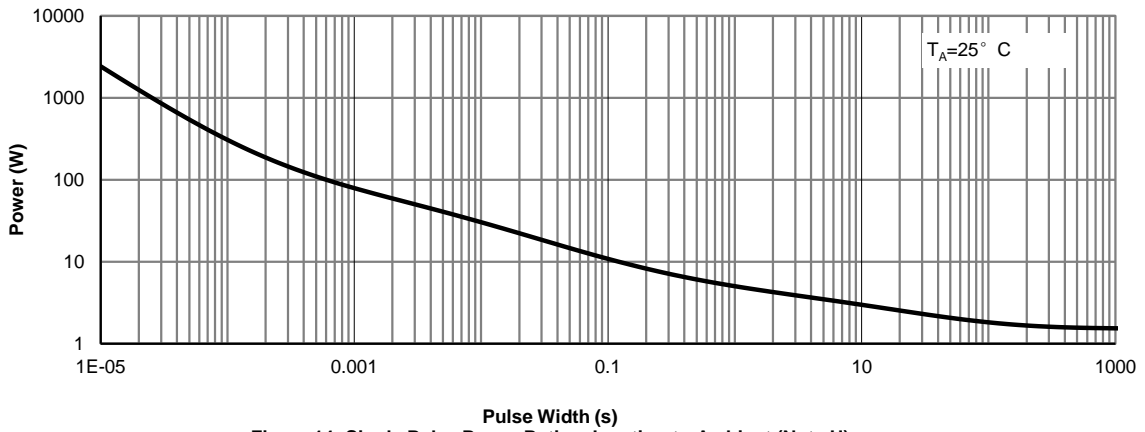


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

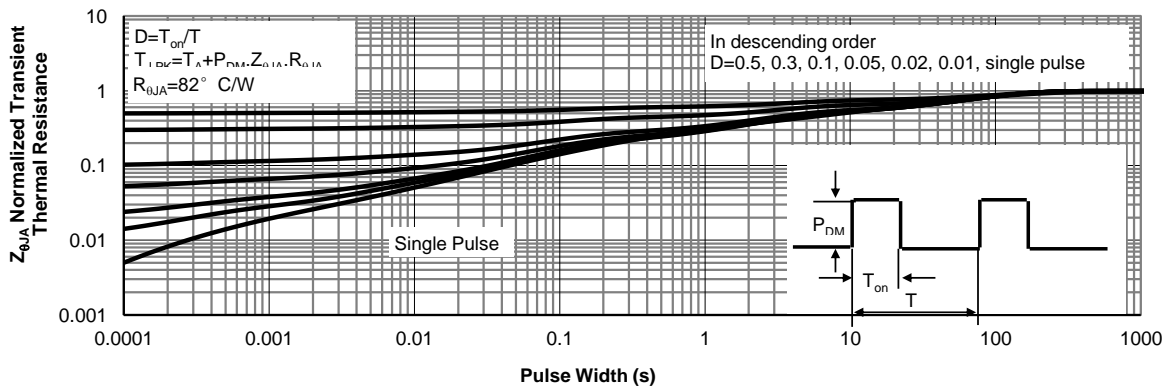


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Q2 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±12V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.1	1.5	1.9	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		3.1	3.8	mΩ
		V _{GS} =4.5V, I _D =20A		4.4	5.4	
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		100		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current ^G				32	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		2005		pF
C _{oss}	Output Capacitance			430		pF
C _{riss}	Reverse Transfer Capacitance			50		pF
R _g	Gate resistance	f=1MHz	1.1	2.2	3.3	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =20A		30	42	nC
Q _{g(4.5V)}	Total Gate Charge			13.5	19	nC
Q _{gs}	Gate Source Charge			5.5		nC
Q _{gd}	Gate Drain Charge			3.5		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω		8		ns
t _r	Turn-On Rise Time			3		ns
t _{D(off)}	Turn-Off DelayTime			34		ns
t _f	Turn-Off Fall Time			5.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=500A/μs		12		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=500A/μs		21		nC

- A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} t_s ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
- B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.
- D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.
- G. The maximum current rating is package limited.
- H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.
- I. For application requiring slow >1ms turn-on/turn-off, please consult AOS FAE for proper product selection.

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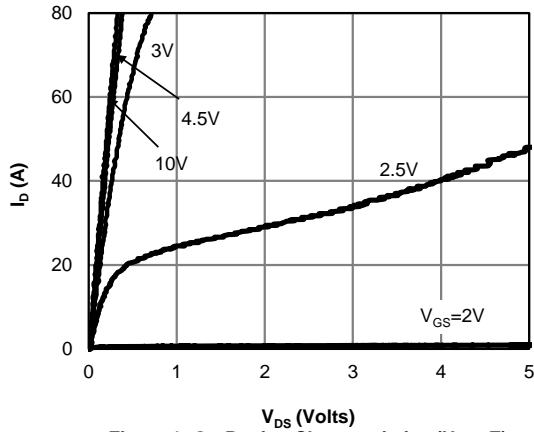


Figure 1: On-Region Characteristics (Note E)

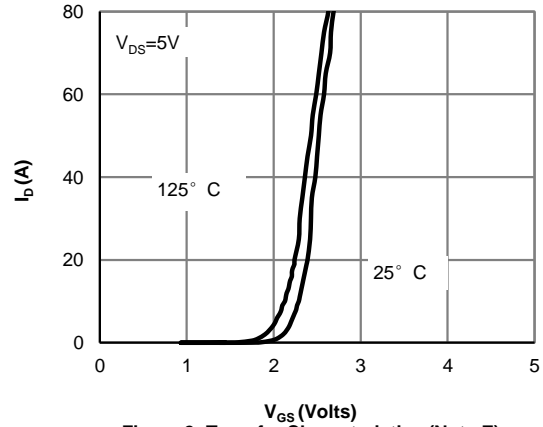


Figure 2: Transfer Characteristics (Note E)

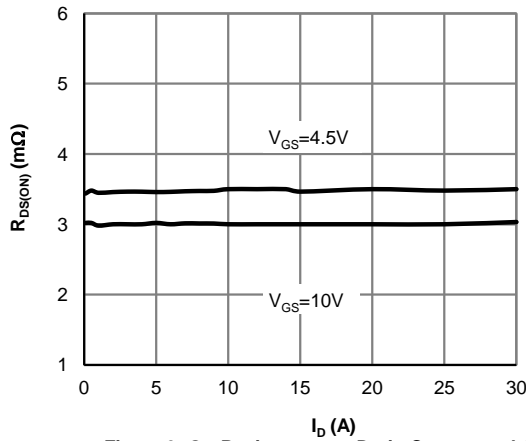


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

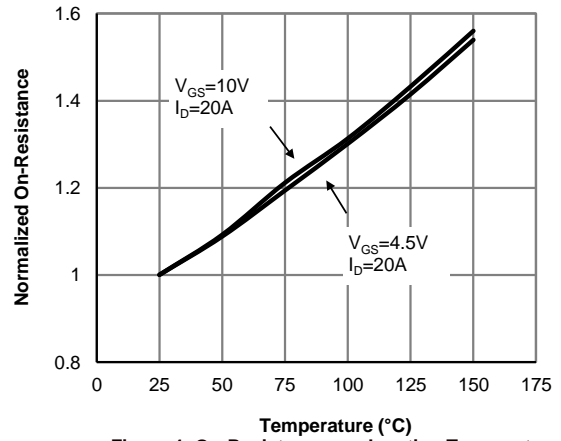


Figure 4: On-Resistance vs. Junction Temperature (Note E)

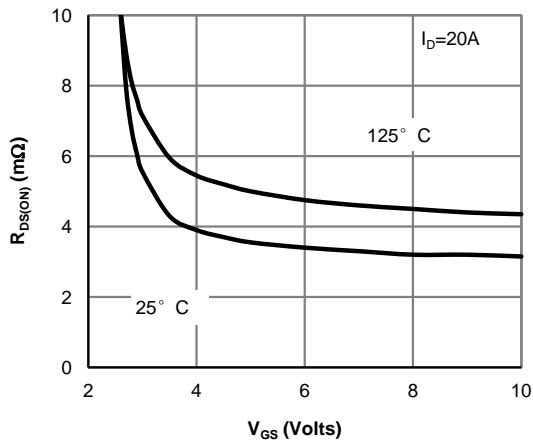


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

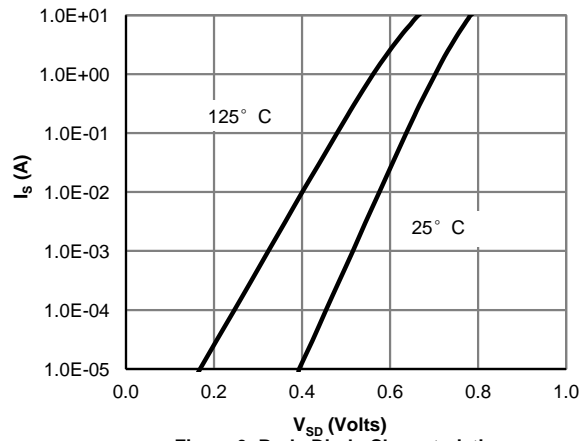


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

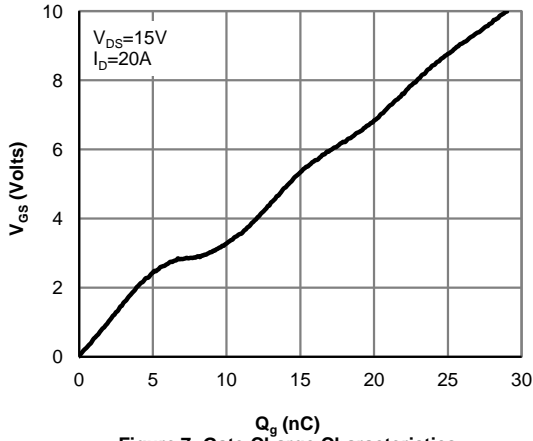


Figure 7: Gate-Charge Characteristics

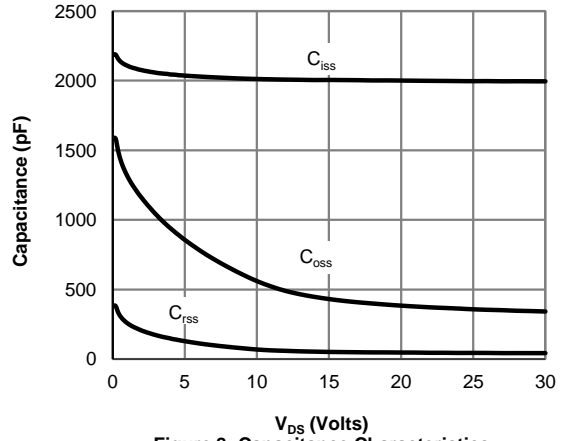


Figure 8: Capacitance Characteristics

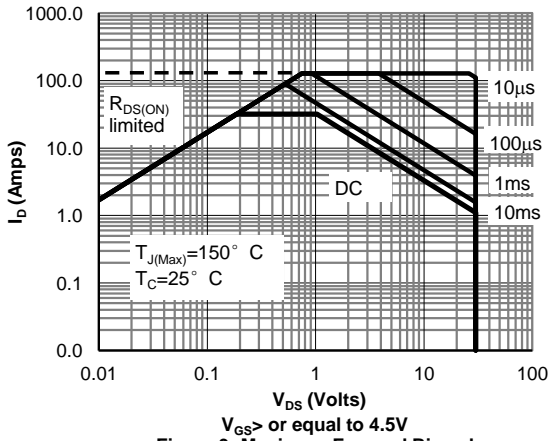


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

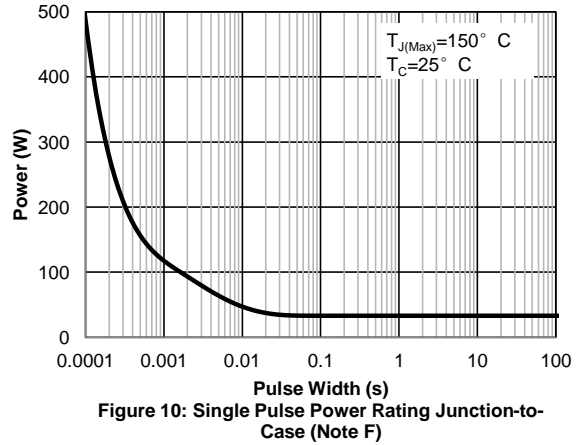


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

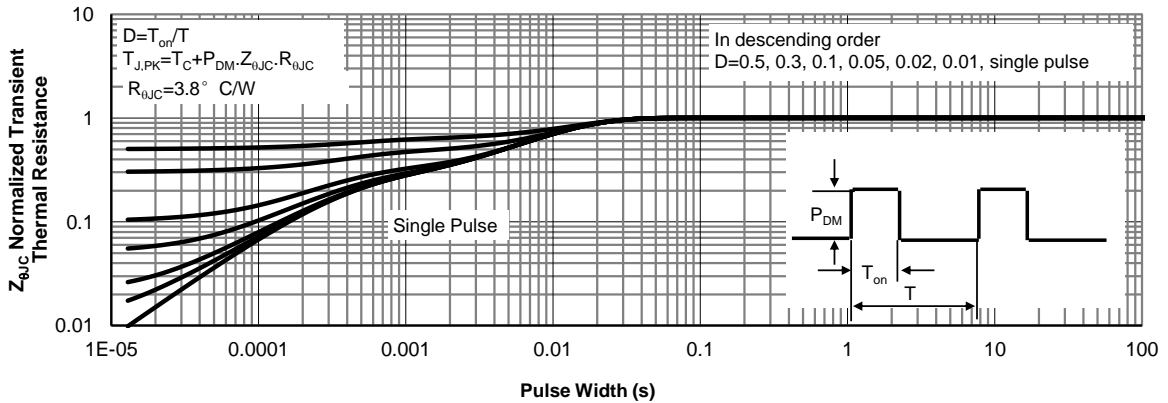


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

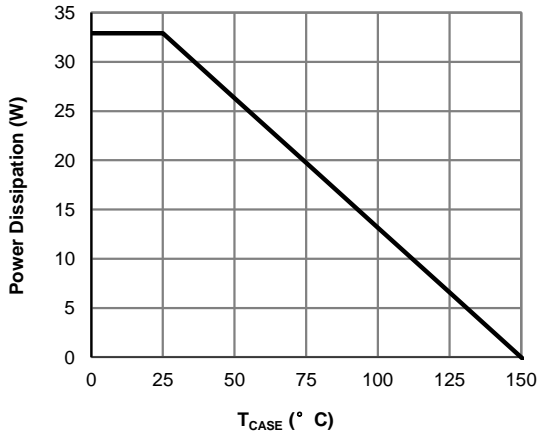


Figure 12: Power De-rating (Note F)

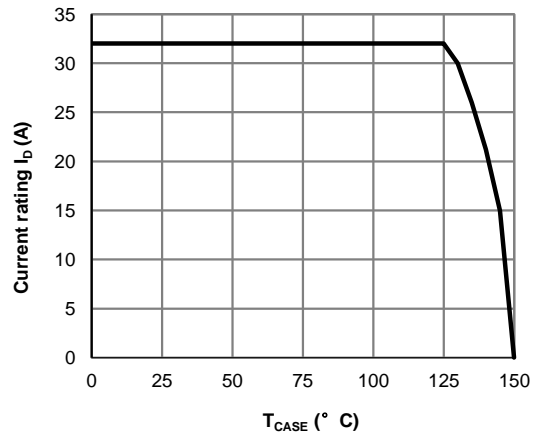


Figure 13: Current De-rating (Note F)

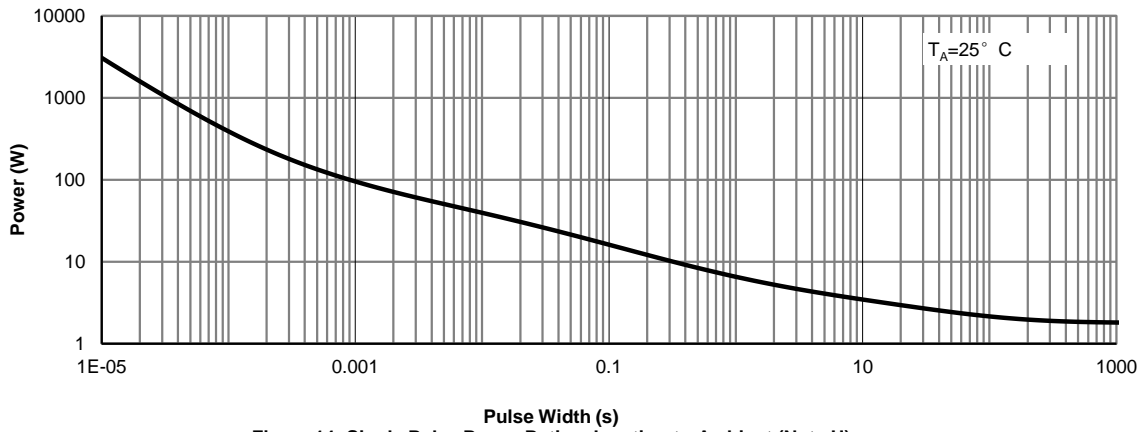


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

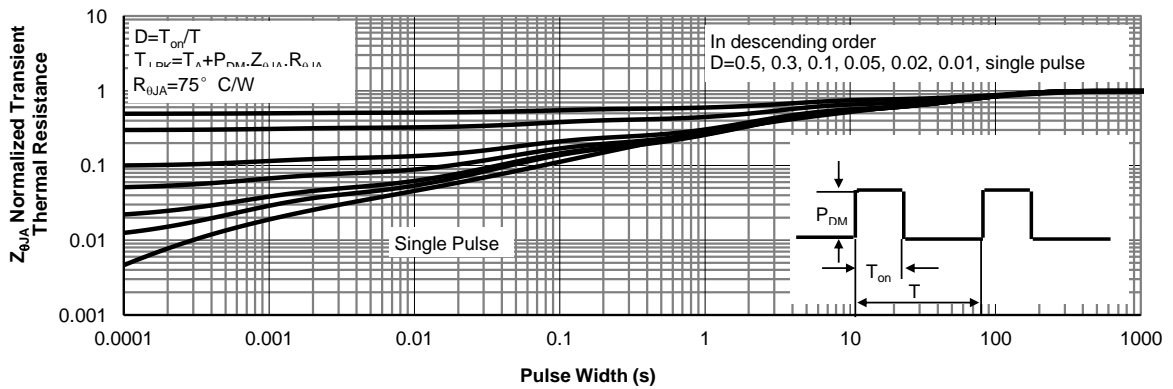


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

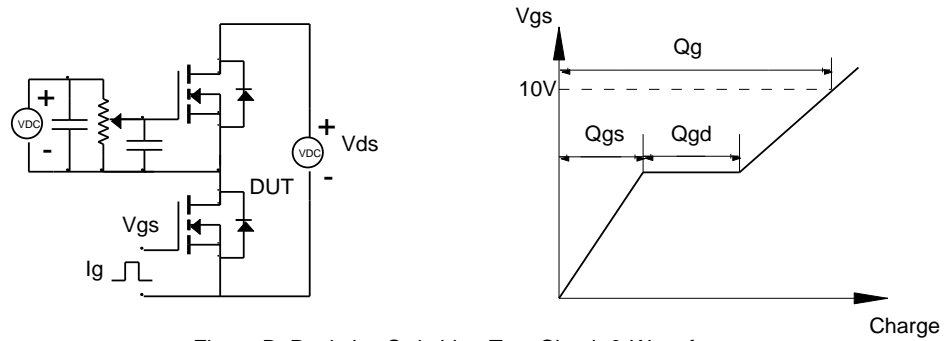


Figure B: Resistive Switching Test Circuit & Waveforms

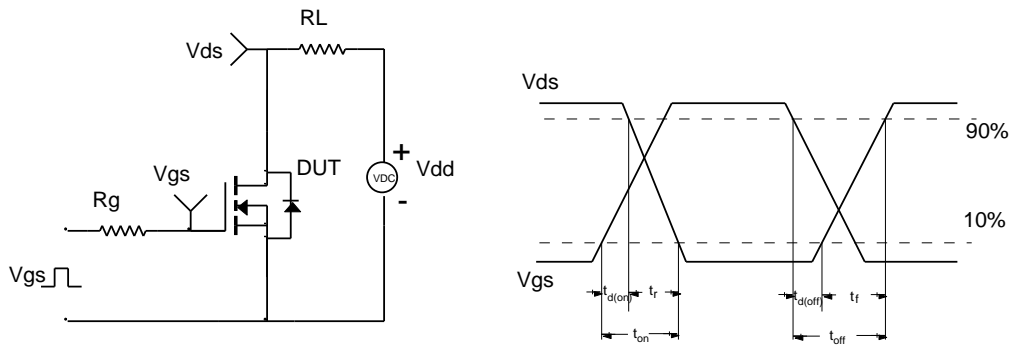


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

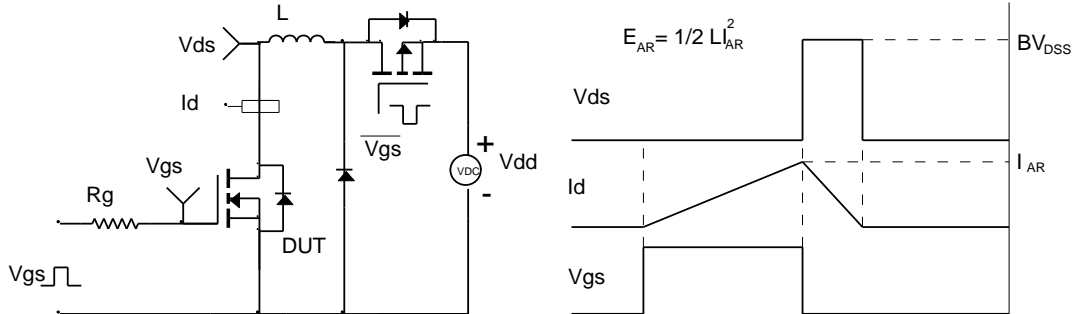
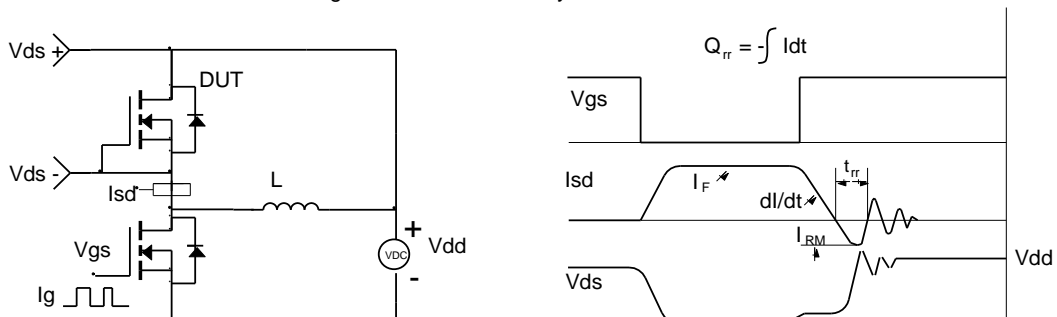


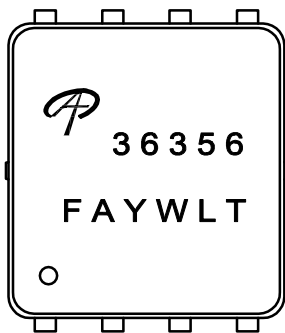
Figure D: Diode Recovery Test Circuit & Waveforms





Document No.	PD-03085
Version	A
Title	AONY36356 Marking Description

DFN5x6 PACKAGE MARKING DESCRIPTION



Green product

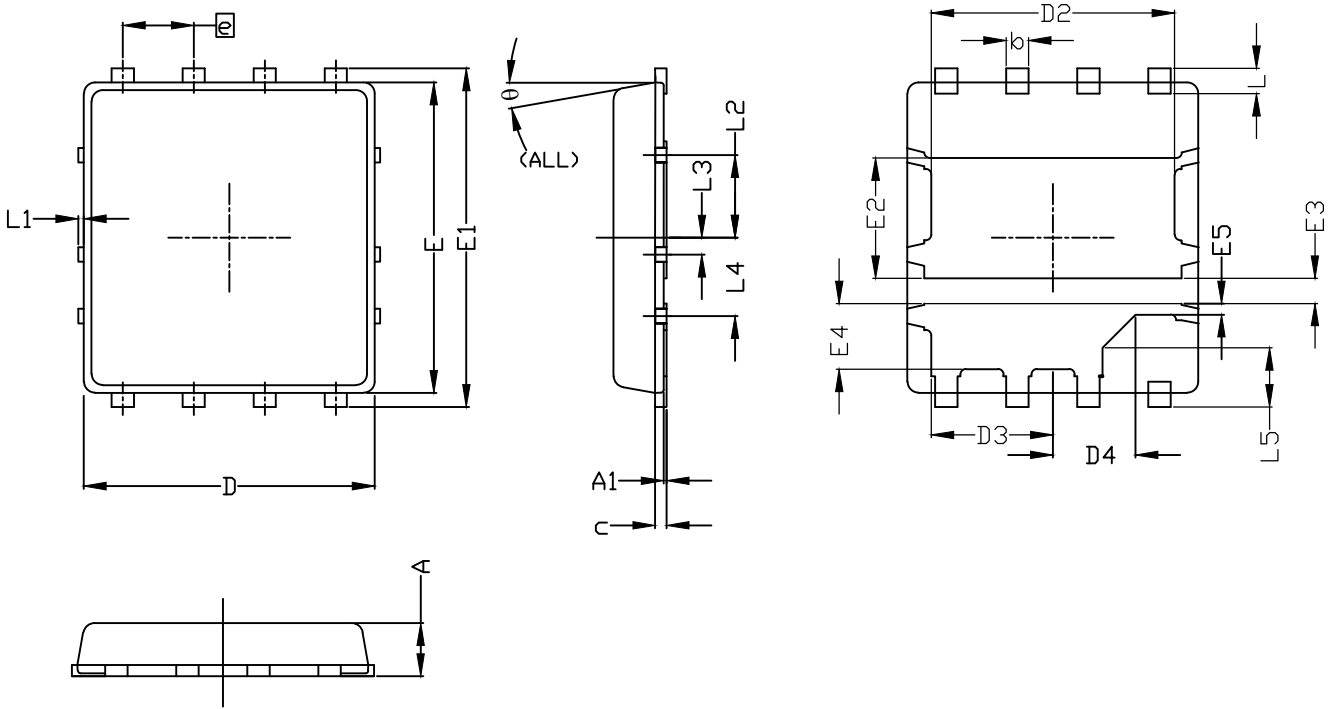
NOTE:

- LOGO - AOS Logo
- 36356 - Part number code
- F - Fab code
- A - Assembly location code
- Y - Year code
- W - Week code
- L&T - Assembly lot code

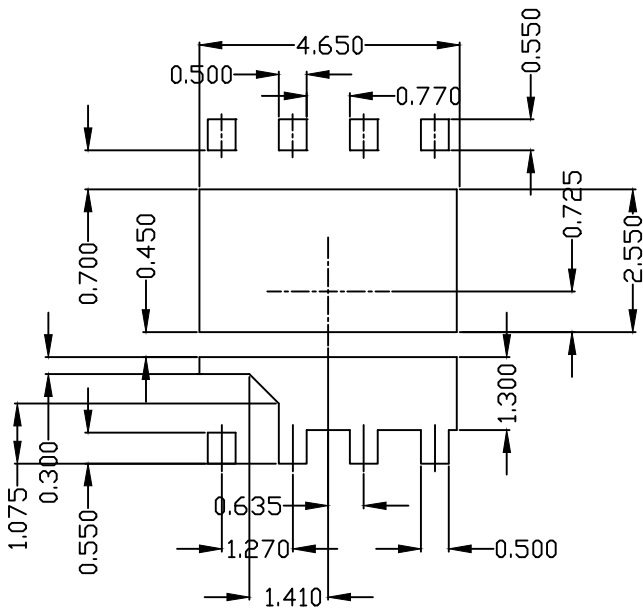
PART NO.	DESCRIPTION	CODE
AONY36356	Green product	36356



DFN5x6D_8L_EP2_P PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.90	1.00	0.033	0.035	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.35	0.40	0.45	0.014	0.016	0.018
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.10	5.20	5.30	0.201	0.205	0.209
D2	4.20	4.35	4.50	0.165	0.171	0.177
D3	2.125	2.175	2.225	0.084	0.086	0.088
D4	1.376	1.476	1.576	0.0542	0.0582	0.0622
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	2.00	2.15	2.30	0.079	0.085	0.091
E3	0.35	0.45	0.55	0.014	0.018	0.022
E4	1.075	1.175	1.275	0.042	0.046	0.050
E5	0.150	0.200	0.250	0.006	0.008	0.010
e	1.27 BSC			0.050 BSC		
L	0.35	0.45	0.55	0.014	0.018	0.022
L1	0	---	0.10	0	---	0.004
L2	1.375	1.475	1.575	0.054	0.058	0.062
L3	0.20	0.30	0.40	0.008	0.012	0.016
L4	1.30	1.40	1.50	0.051	0.055	0.059
L5	0.960	1.060	1.160	0.038	0.042	0.046
θ	0°	---	10°	0°	---	10°

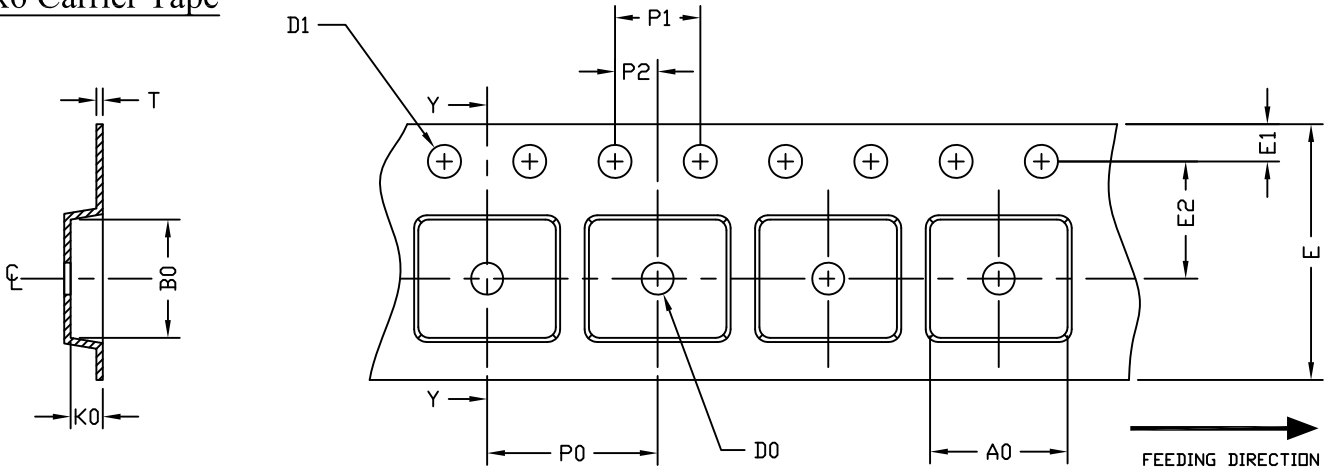
UNIT: mm

NOTE

- PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
- CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.



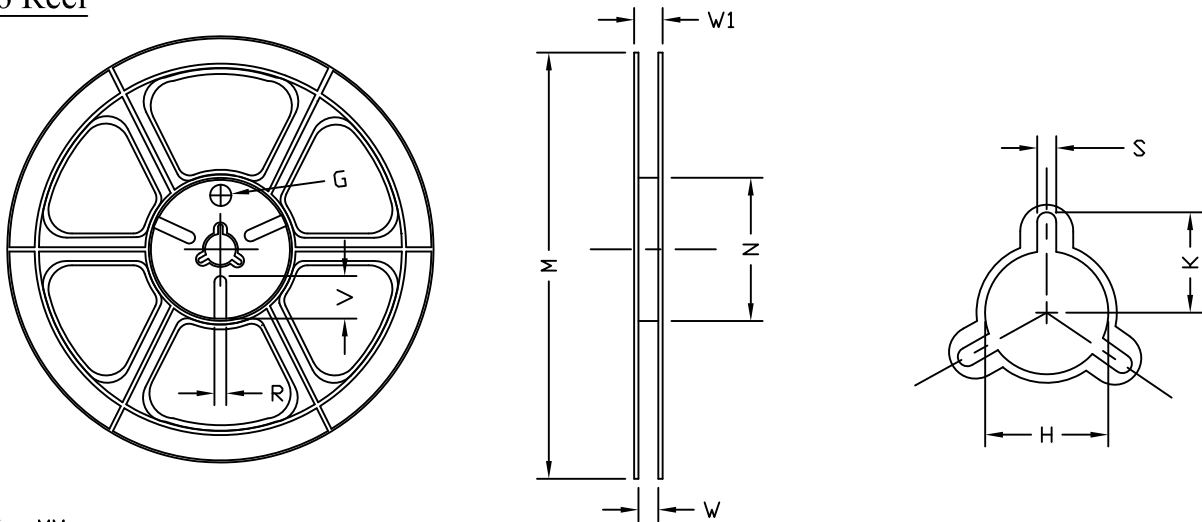
DFN5x6 Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
DFN5x6 (12 mm)	6.30 ±0.10	5.45 ±0.10	1.30 ±0.10	1.50 MIN.	1.55 ±0.05	12.00 ±0.30	1.75 ±0.10	5.50 ±0.10	8.00 ±0.10	4.00 ±0.10	2.00 ±0.10	0.30 ±0.05

DFN5x6 Reel



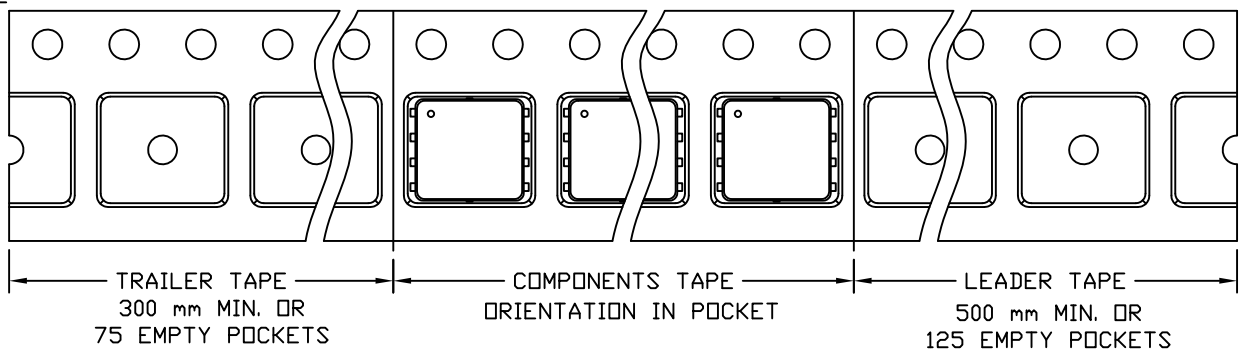
UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	ø330	ø330.00 ±0.50	ø97.00 ±0.10	13.00 ±0.30	17.40 ±1.00	ø13.00 +0.50 -0.20	10.60	2.00 ±0.50	---	---	---

DFN5x6 Tape

Leader / Trailer & Orientation

Unit Per Reel:
3000pcs



单击下面可查看定价，库存，交付和生命周期等信息

[>>AOS\(万国半导体\)](#)